Slotted Optical Switch

OPB852A1-3, OPB853A1-3



Features:

- Inexpensive opaque plastic housing
- Choice of transistor (OPB852) or photodarlington (OPB853) output
- 0.125" (3.18 mm) slot width
- 0.290" (7.37 mm) lead spacing
- Apertured for high resolution



Description:

Slotted optical switches in the OPB852, and OPB853 series consist of an infrared emitting diode and a NPN silicon phototransistor or photodarlington, mounted on opposite sides of a 0.125" (3.175 mm) wide slot. The OPB852A, OPB852B and OPB852C have phototransistor output, while the OPB853A, OPB853B and OPB853C have photodarlington output.

On each of these devices, the emitter has a molded-in aperture of 0.050" x 0.050" (1.270 mm x 1.270 mm) and the phototransistor (OPB852) or photodarlington (OPB853) has a molded-in aperture of 0.010" x 0.050" (0.254 mm x 1.270 mm).

Phototransistor or photodarlington switching occurs when an opaque object passes through the slot.

Applications:

- Non-contact interruptive object sensing
- Assembly line automation
- Machine automation
- Equipment security
- Machine safety





OPB852



OPB853

Description
Anode
Cathode
Collector
Emitter



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

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Electrical Specifications

Absolute Maximum Ratings (T _A =25°C unless otherwise noted)
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Storage	-40°C to +85° C							
Lead So	260° C ⁽¹							
Input Diode								
Forwar	40 m/							
Peak F	37							
Revers	2 \							
Power	100 mW ⁽⁾							
Output Pho	totransistor							
Collect	or-Emitter Voltage						30 \	
Emitte	5 \							
Power	100 mW ⁽²							
Electrical Ch	paracteristics ($T_A = 25^{\circ}C$ unless otherwise no	oted)						
SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	TEST CONDITIONS		
Input Diode	(see OP140 for additional information—OP	B852A_,	OP245 f	or additi	onal infori	mation—OPB853A)		
V _F	Forward Voltage	-	-	1.7	V	I _F = 20 mA		
I _R	Reverse Current	-	-	100	μA	V _R = 2 V		
Output Pho	totransistor (see OP550 for additional infor	mation—	OPB852	A_, OP56	5 for add	itional information—0	DPB853A)	
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage OPB852A1, OPB852A2, OPB852A3 OPB853A1, OPB853A2, OPB853A3	30 15	-		V V	I _c = 1 mA I _c = 1 mA		
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5	-	-	V	I _E = 100 μA		
I _{CEO}	Collector-Emitter Dark Current	-	-	100	nA	$V_{CE} = 10 V$		
Combined	1					I		
combined						I _C = 500 μA, I _F = 20 mA I _C = 1.8 mA, I _F = 20 mA I _C = 1.8 mA, I _F = 10 mA		
V _{CE(SAT)}	Saturation Voltage OPB852A1, OPB852A2 OPB852A3 OPB853A1, OPB853A2, OPB853A3	- -	- -	0.4 0.4 1.0	V V V	$I_{c} = 1.8 \text{ mA}, I_{F} = 20 \text{ m}$	A	

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Performance

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